



PTO/SB/08A (10-01)

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U. S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>			Complete if Known		
			Application Number	10/790,816	
			Filing Date	March 3, 2004	
			First Named Inventor	Terry L. Gilton	
			Art Unit	2812	
			Examiner Name	Not Yet Assigned	
Sheet	1	of	4	Attorney Docket Number	M4065.0607/P607-A

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Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
HD	**AA	2002/0031005	03/2002	Natori et al.	
	**AB	2002/0132417	09/09/2002	Li	
	**AC	2002/0160551	10/31/2002	Harshfield	
	**AD	2002/0168852	11/14/2002	Harshfield et al.	
	**AE	2002/0190289	12/19/2002	Harshfield et al.	
	**AF	2003/0032254	02/13/2003	Gilton	
	**AG	2003/0038301	02/27/2003	Moore	
	**AH	2003/0043631	03/06/2003	Gilton et al.	
	**AI	2003/0045049	03/06/2003	Campbell et al.	
	**AJ	2003/0045054	03/06/2003	Campbell et al.	
	**AK	2003/0047765	03/13/2003	Campbell	
	**AL	2003/0047772	03/13/2003	Li	
	**AM	2003/0047773	03/13/2003	Li	
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	**AO	2003/0049912	03/13/2003	Campbell et al.	
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	**AQ	2003/0068861	04/10/2003	Li	
	**AR	2003/0068862	04/10/2003	Li	
	**AS	2003/0095426	05/22/2003	Hush et al.	
	**AT	2003/0096497	05/22/2003	Moore et al.	
	**AU	2003/0107105	06/12/2003	Kozicki	
	**AV	2003/0117831	06/26/2003	Hush	
	**AW	2003/0128612	07/10/2003	Moore et al.	
	**AX	2003/0137869	07/24/2003	Kozicki	
	**AY	2003/0143782	07/31/2003	Gilton et al.	
	**AZ	2003/0155589	08/21/2003	Campbell et al.	
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	**AB1	2003/0156447	08/21/2003	Kozicki	
	**AC1	2003/0156463	08/21/2003	Casper et al.	
	**AD1	2003/0209728	11/13/2003	Kozicki et al.	
	**AE1	2003/0209971	11/13/2003	Kozicki et al.	
	**AF1	2003/0210564	11/13/2003	Kozicki et al.	
	**AG1	2003/0212724	11/2003	Ovshinsky et al.	
	**AH1	2003/0048744	3/2003	Ovshinsky et al.	
	**AI1	2003/0212725	11/2003	Ovshinsky et al.	
	**AJ1	2004/0035401	2/2004	Ramachandran et al.	
	**AK1	4,804,490	02/14/1989	Pryor et al.	
	**AL1	4,920,078	04/24/1990	Bagley et al.	
	**AM1	5,330,630	07/19/1994	Klersy et al.	
	**AN1	5,814,527	9/29/1998	Wolstenholme et al.	
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	**AR1	5,869,843	2/9/1999	Harshfield	

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#1	**AS1	5,933,365	08/03/1999	Klersy et al.	
	**AT1	5,976,928	11/19999	Kirlin et al.	
	**AU1	6,031,287	2/29/2000	Harshfield	
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	**AY1	RE 37,259E	7/2001	Ovshinsky	
	**AZ1	3,271,591	9/1966	Ovshinsky	
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	**AF2	4,267,261	5/1981	Hallman et al.	
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	**AR2	4,710,899	12/1987	Young et al.	
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	**AY2	4,809,044	2/1989	Pryor et al.	
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			Art Unit	2812	
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Sheet	3	of	4	Attorney Docket Number	M4065.0607/P607-A

(H)	**AP3	5,534,712	7/1996	Ovshinsky et al.	
	**AQ3	5,536,947	7/1996	Klersy et al.	
	**AR3	5,543,737	8/1996	Ovshinsky	
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	**AV3	5,694,054	12/1997	Ovshinsky et al.	
	**AW3	5,714,768	2/1998	Ovshinsky et al.	
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	**AY3	5,912,839	6/1999	Ovshinsky et al.	
	**AZ3	5,933,365	8/1999	Klersy et al.	
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	**AB4	6,087,674	7/2000	Ovshinsky et al.	
	**AC4	6,141,241	10/2000	Ovshinsky et al.	
	**AD4	6,339,544	1/2002	Chiang et al.	
	**AE4	6,404,665	6/2002	Lowery et al.	
	**AF4	6,429,064	8/2002	Wicker	
	**AG4	6,437,383	8/2002	Xu	
	**AH4	6,462,984	10/2002	Xu et al.	
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	**AK4	6,501,111	12/2002	Lowery	
	**AL4	6,507,061	1/2003	Hudgens et al.	
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	**AO4	6,512,241	1/2003	Lai	
	**AP4	6,514,805	2/2003	Xu et al.	
	**AQ4	6,531,373	3/2003	Gill et al.	
	**AR4	6,534,781	3/2003	Dennison	
	**AS4	6,545,287	4/2003	Chiang	
	**AT4	6,545,907	4/2003	Lowery et al.	
	**AU4	6,555,860	4/2003	Lowery et al.	
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	**AW4	6,566,700	5/2003	Xu	
	**AX4	6,567,293	5/2003	Lowery et al.	
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	**AB5	6,586,761	7/2003	Lowery	
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	**AD5	6,590,807	7/2003	Lowery	
	**AE5	6,593,176	7/2003	Dennison	
	**AF5	6,597,009	7/2003	Wicker	
	**AG5	6,605,527	8/2003	Dennison et al.	
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	**AI5	6,621,095	9/2003	Chiang et al.	
	**AJ5	6,625,054	9/2003	Lowery et al.	
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(H)	**AL5	6,646,297	11/2003	Dennison	

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				Art Unit	2812
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				Attorney Docket Number	M4065.0607/P607-A
Sheet	4	of	4		

47	**AM5	6,649,928	11/2003	Dennison	
	**AN5	6,667,900	12/2003	Lowery et al.	
	**AO5	6,671,710	12/2003	Ovshinsky et al.	
	**AP5	6,673,700	1/2004	Dennison et al.	
	**AQ5	6,674,115	1/2004	Hudgens et al.	
	**AR5	6,687,427	2/2004	Ramalingam et al.	
	**AS5	6,690,026	2/2004	Peterson	
	**AT5	6,696,355	2/2004	Dennison	
	**AU5	6,687,153	2/2004	Lowery	
	**AV5	6,707,712	3/2004	Lowery	
	**AW5	6,714,954	3/2004	Ovshinsky et al.	
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Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patenteo or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ^c
		Country Code ² -Number ⁴ -Kind Code ⁶ <i>(if known)</i>				

Examiner Signature	<i>Heather Don</i>	Date Considered	10/25/05
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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete If Known	
				Application Number	10/121,792 10/790 816
				Filing Date	April 10, 2002 3/3/04
				First Named Inventor	Terry L. Gilton
				Art Unit	1773
				Examiner Name	Not Yet Assigned
Sheet	1	of	10	Attorney Docket Number	M4065.0607/P607

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Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
HD	AA	6,388,324**	05/14/2002	Kozicki et al.	
	AB	US 2002/0000666**	01/03/2002	Kozicki et al.	
	AC	5,500,532**	03/19/1996	Kozicki et al.	
	AD	6,418,049**	07/09/2002	Kozicki et al.	
	AE	5,751,012**	05/12/1998	Wolstenholme et al.	
	AF	5,789,277**	08/04/1998	Zahorik et al.	
	AG	6,348,365**	02/19/2002	Moore et al.	
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	AC1	5,219,788**	6/1993	Abernathay et al.	
	AD1	5,238,862**	8/1993	Bialock et al.	
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	AF1	5,350,484**	9/1994	Gardner et al.	
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	AH1	5,512,328**	4/1996	Yoshimura et al.	
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	AN1	5,920,788**	7/1999	Reinberg	
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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete If Known	
				Application Number	40/121,702
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				Art Unit	1773
				Examiner Name	Not Yet Assigned
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41)	AT1	6,236,059**	5/2001	Wolstenholme et al.	
	AU1	6,297,170**	10/2001	Gabriel et al.	
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	AE2	5,314,772**	5/24/1994	Kozicki	
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	AG2	2003/0027416 APP**	2/6/2003	Moore	
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	AP2	4,800,526**	1/89	Lewis	
	AQ2	2003/00353**14	02/20/03	Kozicki	
	AR2	2003/003531**5	02/20/03	Kozicki	
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41)	BB	WO 00/48196**		08/17/2000	Kozicki et al.		
41)	BC	WO 97/48032**		12/18/1997	Kozicki et al.		
41)	BD	WO 99/28914**		06/10/1999	Kozicki et al.		
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Examiner Signature	Heather Doty	Date Considered	10/25/05
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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS				
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²	
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Sheet	4	of	10	Attorney Docket Number	M4065.0607/P607

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		Filing Date	April 10, 2002		
		First Named Inventor	Terry L. Gilton		
		Group Art Unit	1773		
		Examiner Name	Not Yet Assigned		
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		Application Number	10/121,791 10/790 816		
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		First Named Inventor	Terry L. Gilton		
		Group Art Unit	1773		
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Examiner Signature	<i>Heather Doty</i>	Date Considered	10/25/06
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